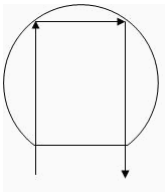
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none or SEMI Standard	Wafer Vendor
	5.0	Overall Thickness	525.00 +/- 25.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00µm	Guaranteed by Process
	7.0	Bow	<40.00 µm	ADE to ASTM F534, 20%
	8.0	Warp	40.00 +/- 0.00 µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	13.0	Handle Thickness	525.00 +/- 25.00 µm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Any	Wafer Vendor
	16.0	Handle Resistivity	0.005 ~ 0.02 Ohm-cm	Wafer Vendor
	17.0	Backside Finish	Lapped / Etched with Oxide and laser mark	Guaranteed by process
OverallWafer	18.0	Field Oxidation	10,000.00 +/- 1,000.00 A	Nanospec centre point, 4%

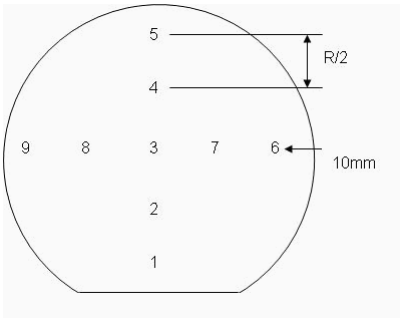
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information